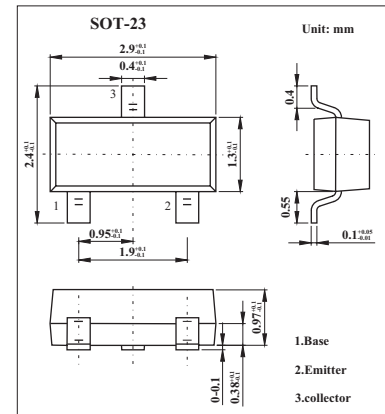


## Silicon PNP Epitaxial

## 2SA1313

## ■ Features

- High voltage:  $V_{CE0} = -50$  V (min)
- Small package

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-500	mA
Base current	$I_B$	-50	mA
Collector power dissipation	$P_C$	200	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50$ V, $I_E = 0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5$ V, $I_C = 0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -1$ V, $I_C = -100$ mA	70		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100$ mA, $I_B = -10$ mA		-0.1	-0.25	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -1$ V, $I_C = -100$ mA		-0.8	-1	V
Transition frequency	$f_T$	$V_{CE} = -6$ V, $I_C = -20$ mA		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -6$ V, $I_E = 0$ , $f = 1$ MHz		13		pF

■  $h_{FE}$  Classification

Marking	AC	
	Rank	O
$h_{FE}$	70~140	120~240